

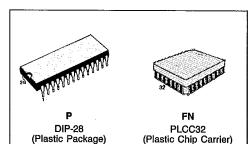
TS27C64AFN TS27C64AP

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64K (8K×8) CMOS ONE TIME PROGRAMMABLE ROM

- COMPATIBLE TO TS27C64A EPROM (ELECTRICAL PARAMETERS, PROGRAMMING)
- PROGRAMMING VOLTAGE 12.5V
- HIGH SPEED PROGRAMMING
- 28-PIN JEDEC APPROVED PIN-OUT
- 32-PIN JEDEC APPROVED PIN-OUT (PLCC)
- IDEAL FOR AUTOMATIC INSERTION



(Ordering Information at the end of the datasheet)

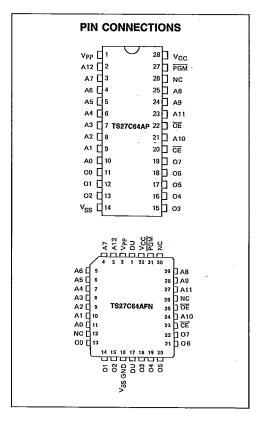
DESCRIPTION

The TS27C64AP and TS27C64AFN are high speed 65,536-bit One Time Programmable (OTP) CMOS ROM ideally suited for applications where fast turnaround is an important requirement.

The TS27C64AP is packaged in a 28-pin dual-inline plastic package, the TS27C64AFN in a 32-pin PLCC plastic package and therefore can not be rewritten. Programming is performed according to standard SGS-THOMSON 64K EPROM procedure.

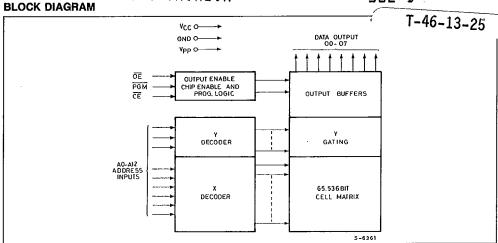
PIN NAMES

A0—A12	ADDRESS	
CE	CHIP ENABLE	
ŌĒ	OUTPUT ENABLE	
O ₀ -O ₇	OUTPUTS	
PGM	PROGRAM	
NC	NON CONNECTED	
DU	DO NOT USE	



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ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
T _{amb}	Operating temperature range TS27C64A-C TS27C64A-V TS27C64A-T	T _L to T _H 0 to + 70 - 40 to + 85 - 40 to + 105	°C
T _{stg}	Storage temperature range	65 to + 125	°C
V _{PP} ⁽²⁾	Supply voltage	-0.6 to +14	٧
V _{IN⁽²⁾}	Input voltages A9 Except V _{PP} , A9	-0.6 to +13.5 -0.6 to +6.25	V
PD	Max power dissipation	1.5	W
	Lead temperature (Soldering: 10 seconds)	+300	°C

Notes: 1. "Maximum ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating temperature range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical characteristics" provides conditions for actual device operation.

2. With respect to GND

OPERATING MODES

PINS	CE	ŌĒ	A9	PGM	V _{PP}	v _{cc}	OUTPUTS
READ	V _{IL}	V _{IL}	Х	V _{IH}	Vcc	V _{CC}	D _{OUT}
OUTPUT DISABLE	V _{IL}	V _{IH}	Х	VIH	V _{CC}	Vcc	Hi-Z
STANDBY	V _{IH}	Х	Х	Х	Vcc	Vcc	Hi-Z
HIGH SPEED PROGRAMMING	V _{IL}	VIH	Х	V _{IL}	V _{PP}	Vcc	D _{IN}
PROGRAM VERIFY	V _{IL}	V _{IL}	Х	V _{IH}	V _{PP}	V _{CC}	D _{OUT}
PROGRAM INHIBIT	V _{IH}	Х	· X	Х	V _{PP}	V _{CC}	Hi-Z
ELECTRONIC SIGNATURE(3)	V _{IL}	V _{IL}	VH ⁽²⁾	V _{IH}	Vcc	V _{CC}	CODE

Notes: 1. X can be either V_{IL} or V_{IH} — 2. V_{H} = 12.0V \pm 0.5V 3. All address lines at V_{IL} except A9 and A0 that is toggled from V_{IL} (manufacturer code: 9B) to V_{IH} (type code: 08).

READ OPERATION

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DC CHARACTERISTICS ($T_{amb} = T_L$ to T_H , $V_{CC} = 5V \pm 10\%$, GND = 0V; Unless otherwise specified)

Symbol	Parameter	Test Conditions				
Syllibol	raia:iletei	rest Conditions	Min.	Typ. ⁽¹⁾	Max.	Unit
ILI	Input Load Current	V _{IN} =V _{CC} or GND			10	μΑ
ILO	Output Leakage Current	V _{OUT} =V _{CC} or GND, CE=V _{IH}			10	μА
V _{PP}	V _{PP} Read Voltage		V _{CC} -0.7		V _{CC}	٧
V _{IL}	Input Low Voltage		-0.1		0.8	٧
V _{IH}	Input High Voltage		2.0		V _{CC} +1	٧
V _{OL}	Output Low Voltage	I _{OL} =2.1 mA I _{OL} =0 μA			0.45 0.1	٧
V _{OH}	Output High Voltage	$I_{OH} = -400 \mu A$ $I_{OH} = 0 \mu A$	2.4 V _{CC} -0.1			٧
I _{CC2}	V _{CC} Supply Active Current TTL Levels	CE = OE = V _{IL} , Inputs = V _{IH} or V _{IL} , f = 5 MHz, I/O = 0 mA		10	30	mA
I _{CCSB1}	V _{CC} Supply Standby Current	CE = V _{IH}		0.5	1	mA
I _{CCSB2}	V _{CC} Supply Standby Current	CE=V _{CC}		10	100	μА
I _{PP1}	V _{PP} Read Current	$V_{PP} = V_{CC} = 5.5V$			100	μΑ

Note: 1. Typical conditions are for operation at: $T_{amb} = +25$ °C, $V_{CC} = 5V$, $V_{PP} = V_{CC}$, and $V_{SS} = 0V$

AC CHARACTERISTICS(1)(Tamb = T1 to T11)

Symbol Para	Parameter	Test Conditions	27C64A -15		27C64A -20		27C64A -25		27C64A -30		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
tACC	Address to Output Delay	CE = OE = VIL		150		200		250		300	ns
tCE	CE to Output Delay	OE = V _{IL}		150		200		250		300	ns
^t OE	Output Enable to Output Delay	CE=V _{IL}		75		80		100		120	ns
t _{DF} (2,4)	OE or CE High to	CE = V _{IL}	0	50	0	50	0	60	0	105	ns
tон	Output Hold from addresses, CE or OE whichever occured first	CE = OE = V _{IL}	0		0		0		0		ns

CAPACITANCE T_{amb} = +25°C, f = 1 MHz (Note 3)

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Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
Cin	Input Capacitance	V _{IN} = 0V		4	6	pF	
Cout	Output Capacitance	V _{OUT} =0V		8	12	pF	

Notes: 1. V_{CC} must be applied at the same time or before Vpp and removed after or at the same time as Vpp•Vpp may be connected to V_{CC} except during program.

2. The tpp compare level is determined as follows:

High to THREE-STATE, the measured V_{OH}(DC) - 0.1V

Low to THREE-STATE the measured V_{OH}(DC) + 0.1V.

3. Capacitance is guaranteed By periodic testing. T_{amb} = +25°C, f=1MHz.

4. T_{DP}, is specified from OE or CE whichever occurs first. This parameter is only sampled and not 100% tested.

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AC TEST CONDITIONS

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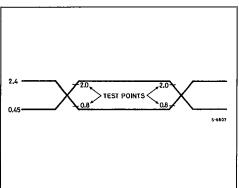
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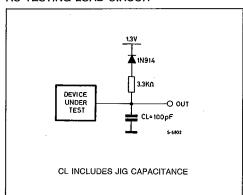
1 TTL gate and CL = 100 pF Output Load: Input Rise and Fall Times ≤20 ns 0.45V to 2.4V Input pulse levels:

Timing Measurement Reference Level Inputs, Outputs 0.8V and 2V

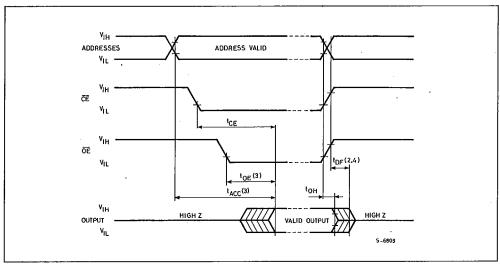
AC TESTING INPUT/OUTPUT WAVEFORM



AC TESTING LOAD CIRCUIT



AC WAVEFORMS



Notes:

- 1. Typical values are for T_{amb} = 25°C and nominal supply voltage
 2. This parameter is only sampled and not 100% tested.
 3. OE may be delayed up to tacc toe after the falling edge CE without impact on tacc
 4. Up;is specified form OE or CE whichever occurs first.

S G S-THOMSON DEVICE OPERATION

The seven modes of operation of the TS27C64A are listed in the Operating Modes table. A single 5V power supply is required in the read mode. All inputs are TTL levels except for V_{DD}.

READ MODE

The TS27C64A has two control functions, both of wich must be logically active in order to obtain data at the outputs. Chip Enable (CE) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from CE to Output (t_{CE}). Data is available at the outputs after a delay of t_{OE} from the falling edge of OE, assuming that CE has been low and addresses have been stable for at least t_{ACC}-t_{OE}.

STANDBY MODE

The TS27C64A has a standby mode which reduces the maximum power dissipation to 5.5 mW. The TS27C64A is placed in the standby mode by applying a TTL high signal to the $\overline{\text{CE}}$ input. When in standby mode, the outputs are in a high impedance state, independent of the $\overline{\text{OE}}$ input.

OUTPUT OR-TYING

Because OTPs are usually used in larger memory arrays, we have provided two control lines which accomodate this multiple memory connection. The two control lines allow for:

- a) the lowest possible memory power dissipation,
- b) complete assurance that output bus contention will not occur.

To use these control lines most efficiently, CE should be decoded and used as the primary device selecting function, while \overline{OE} should be made a common connection to all devices in the array and connected to the \overline{READ} line from the system control bus. This assures that all deselected memory devices are in their low power standby modes and that the output pins are active only when data is desired from a particular memory device.

PROGRAMMING

Caution: Exceeding 14V on V_{pp} pin will damage the TS27C64A.

Initially, all bits of the TS27C64A are in the "1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be presented in the data word.

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The TS27C64A is in the programming mode when the V_{pp} input is at 12.5 V and CE and PGM are both at TTL Low. It is required that a 0.1 μ F capacitor be placed across V_{pp} , V_{CC} and ground to suppress spurious voltage transients which may damage the device. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs

Programming of multiple TS27C64As in parallel with the same data can be easily accomplished due to the simplicity of the programming requirements. Like inputs of the parallel TS27C64As may be connected together when they are programmed with the same data. A low level TTL pulse applied to the PGM input programs the paralleled TS27C64As.

HIGH SPEED PROGRAMMING

The high speed programming algorithm described in the flow chart rapidly programs TS27C64A using an efficient and reliable method particularly suited to the production programming environment. Typical programming times for individual devices are on the order of 1 minute.

PROGRAM INHIBIT

Programming of multiple TS27C64As in parallel with different data is also easily accomplished by using the program inhibit mode. A high level on CE or PGM inputs inhibits the other TS27C64As from from being programmed. Except for CE, all like inputs (including OE) of the parallel TS27C64As may be common. A TTL low-level pulse applied to a TS27C64A CE and PGM inputs with Vpp at 12.5 V will program that TS27C64A.

PROGRAM VERIFY

A verify may be performed on the programmed bits to determine that they were correctly programmed. The verify is performed with \overrightarrow{CE} and \overrightarrow{OE} at V_{IL} , PGM at V_{IH} and V_{pp} at 12.5 V.

ELECTRONIC SIGNATURE MODE

Electronic signature mode allows the reading out of a binary code that will indentify the EPROM manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ±5°C ambient temperature range that is required when programming the TS27C64A. To activate this mode the programming equipment must force 11.5V to 12.5V on address line A9 of the TS27C64A. Two bytes may then be sequenced from the device outputs by toggling address line A0 from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during electonic signature mode.

PROGRAMMING OPERATIONS(1)($T_{amb} = 25 \pm 5$ °C, $V_{CC} = 6.0V \pm 0.25V$, $V_{PP} = 12.5V \pm 0.3V$)

DC AND OPERATING CHARACTERISTICS

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Symbol	Parameter	Test Conditions	Values				
Symbol	Parameter	rest Conditions	Min.	Тур.	Max.	Unit	
lį	Input Current (all inputs)	V _I =V _{IL} or V _{IH}			10	μА	
V _{IL}	input Low Level (all inputs)	·	-0.1		0.8	٧	
V _{IH}	Input High Level		2.0		V _{CC} +1	٧	
VOL	Output low voltage during verify	I _{OL} = 2.1 mA			0.45	V	
v_{OH}	Output high voltage during verify	I _{OH} = -400 μA	2.4			V	
Іссз	V _{CC} Supply current (Program & Verify)				30	mA	
I _{PP2}	V _{PP} supply current (Program)	CE = V _{IL} = PGM		<u> </u>	30	mA	

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AC CHARACTERISTICS

Symbol	Parameter	Test Conditions		11-14			
Symbol	Farameter	rest Conditions	Min.	Тур.	Max.	Unit	
t _{AS}	Address Set-up Time		2			μS	
toes	OE Set-up Time		2			μS	
tos	Data Set-up Time		2			μS	
t _{AH}	Address Hold Time		0			μs	
t _{DH}	Data Hold Time		2			μS	
t _{DFP}	Output enable to output float delay		0		130	ns	
typs	V _{PP} set-up time		2			μS	
tvcs	V _{CC} set-up time		2			μS	
tpw	PGM initial program pulse width		0.95	1.0	1.05	ms	
topw ⁽²⁾	PGM overprogram pulse width		2.85		78.75	ms	
tCES	CE set-up time	····	2			μS	
toE	Data valid from OE				150	ns	

Notes: 1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.

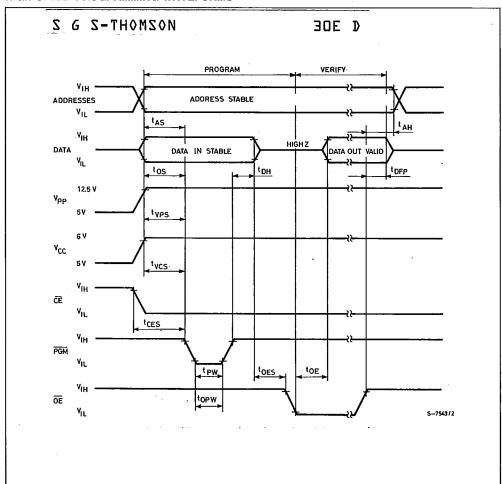
2. topw is defined in flow chart.

AC TEST CONDITIONS

Input rise and fall times (10% to 90%) Input pulse levels 0.45V to 2.4V Input timing reference level 0.8V and 2.0V Output timing reference level 0.8V and 2.0V

HIGH SPEED PROGRAMMING WAVEFORMS

T-46-13-25

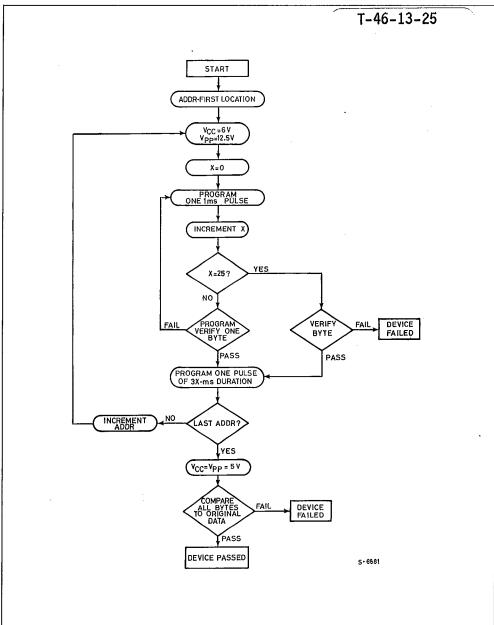


can damage the device.

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HIGH SPEED PROGRAMMING FLOW CHART



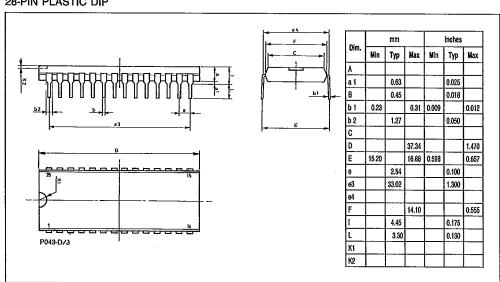
ORDERING INFORMATION (TS27C64AP; Z G Z-THOMZON

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Part Number	Number Access Time		Temp. Range	Package
TS27C64A-15CP	150 ns	5V±10%	0 to + 70°C	DIP-28
TS27C64A-20CP	200 ns	5V±10%	0 to + 70°C	DIP-28
TS27C64A-25CP	250 ns	5V±10%	0 to + 70°C	DIP-28
TS27C64A-30CP	300 ns	5V±10%	0 to + 70°C	DIP-28
TS27C64A-15VP	150 ns	5V ± 10%	-40 to + 85°C	DIP-28
TS27C64A-20VP	200 ns	5V±10%	-40 to + 85°C	DIP-28
TS27C64A-25VP	250 ns	5V±10%	-40 to + 85°C	DIP-28
TS27C64A-30VP	300 ns	5V ± 10%	-40 to + 85°C	DIP-28
TS27C64A-15TP	150 ns	5V±10%	-40 to +105°C	DIP-28
TS27C64A-20TP	200 ns	5V±10%	-40 to +105°C	DIP-28
TS27C64A-25TP	250 ns	5V±10%	-40 to +105°C	DIP-28
TS27C64A-30TP	300 ns	5V±10%	-40 to +105°C	DIP-28

PACKAGE MECHANICAL DATA

28-PIN PLASTIC DIP



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ORDERING INFORMATION (TS27C64AFN)

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Part Number	Access Time	Supply Voltage	Temp. Range	Package	
TS27C64A-15CFN	150 ns	5V±10%	0 to + 70°C	PLCC32	
TS27C64A-20CFN	200 ns	5V ± 10%	0 to + 70°C	PLCC32	
TS27C64A-25CFN	250 ns	5V ± 10%	0 to + 70°C	PLCC32	
TS27C64A-30CFN	300 ns	5V ± 10%	0 to + 70°C	PLCC32	
TS27C64A-15VFN	150 ns	5V ± 10%	-40 to + 85°C	PLCC32	
TS27C64A-20VFN	200 ns	5V±10%	-40 to + 85°C	PLCC32	
TS27C64A-25VFN	250 ns	5V±10%	-40 to + 85°C	PLCC32	
TS27C64A-30VFN	300 ns	5V ± 10%	-40 to + 85°C	PLCC32	
TS27C64A-15TFN	150 ns	5V±10%	-40 to +105°C	PLCC32	
TS27C64A-20TFN	200 ns	5V ± 10%	-40 to +105°C	PLCC32	
TS27C64A-25TFN	250 ns	5V ± 10%	-40 to +105°C	PLCC32	
TS27C64A-30TFN	300 ns	5V ± 10%	-40 to +105°C	PLCC32	

PACKAGE MECHANICAL DATA

PLCC32 32-LEAD PLASTIC LEADED CHIP CARRIER

